IDS #0705

Form PTO-1449 (REV. 8-83)	US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 119232	APPLICATION NO. 10/807,235
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT(S) Akira SAKAI et al.	
		FILING DATE March 24, 2004	GROUP 2826

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
GP	1	JP 2002-289843 (w/English abstract & machine translation)	10/4/2002	JAPAN	—	—

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

EXAMINER	Evan Pert	DATE CONSIDERED	11/3/05

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: July 7, 2005

IDS #1005

Sheet 1 of 1

Form PTO-1449 (REV. 8-83) US Dept. of Commerce PATENT & TRADEMARK OFFICE	ATTY DOCKET NO. 119232	APPLICATION NO. 10/807,235
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)	APPLICANT(S) Akira SAKAI et al.	
	FILING DATE March 24, 2004	GROUP 2826

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS
EP	1.	6,509,283	01-21-2003	Thomas	—	—
EP	2.	2003/0020068 A1	01-30-2003	Finder	—	—
EP	3.	2002/0197793 A1	12-26-2002	Dornfest et al.	—	—

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

EP	4.	European Search Report dated September 19, 2005
EP	5.	Osten, et al., Epitaxial Praseodymium Oxide: A new high-K dielectric, pp. 100-106, JWGI (2001)
EP	6.	Liu, et al., Epitaxial growth of Pr_2O_3 on Si(111) and the observation of a hexagonal to cubic phase transition during postgrowth N_2 annealing, 79(5):671-673, Applied Physics Letters (July 30, 2001)
EP	7.	Ferrari, et al., Chlorine mobility during annealing in N_2 in ZrO_2 and HfO_2 films grown by atomic layer deposition, 92(12):7675-7677, J. of Applied Physics (December 15, 2002)
EP	8.	Murawala, et al., Plasma Enhanced Liquid Source-CVD and Rapid Thermal Annealing of Tantalum Penta Oxide Dielectric Material, Materials, Tsukuba, pp. 527-529 (1992)
EP	9.	Mereu, et al., Fowler-Nordheim Tunneling in Epitaxial Yttrium Oxide on Silicon for High-K Gate Applications, Proceedings of the IEEE International Semiconductor Conference, 2:309-312 (October 8, 2002)

EXAMINER	Evan Pert	DATE CONSIDERED	11/3/05

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Date: October 31, 2005